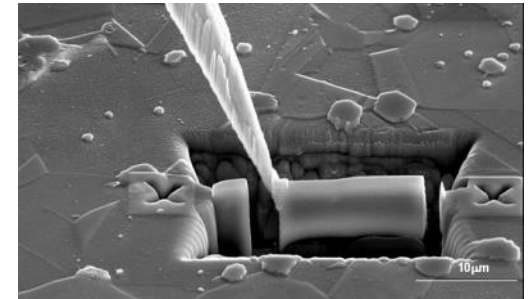
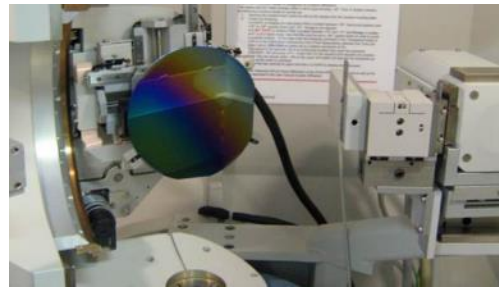
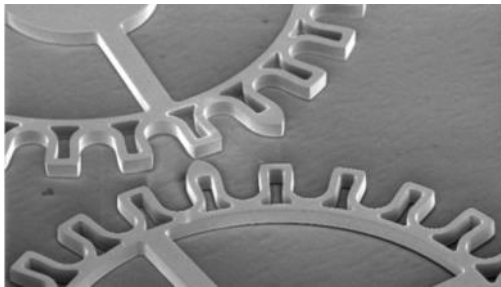


# Advanced materials characterization using state-of-the-art microscopy and XRD techniques focusing on the relationship between microstructural and mechanical properties

**EIROforum WAMAS**, CERN, 20<sup>th</sup> of November 2013

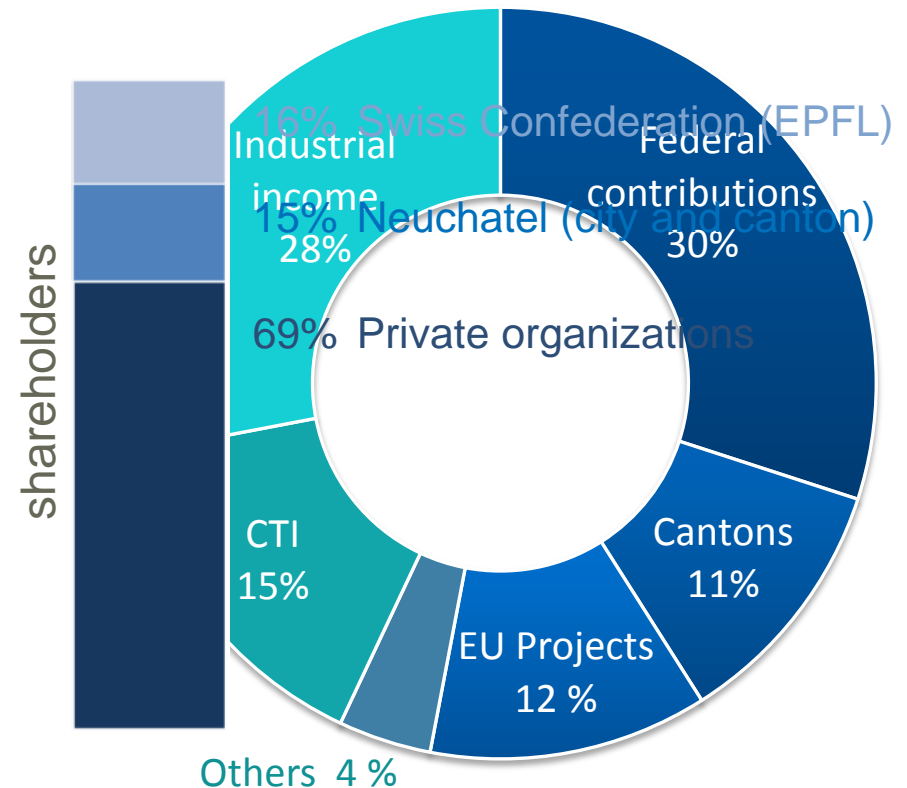
**Laboratory for X-Ray Applications & Microscopy,  
Microsystem Technology**

**X. Maeder, A. Neels, M. Dadras, O. Sereda, M. Garganourakis,  
T. Bandi, M. Lebeouf, S. Biselli**

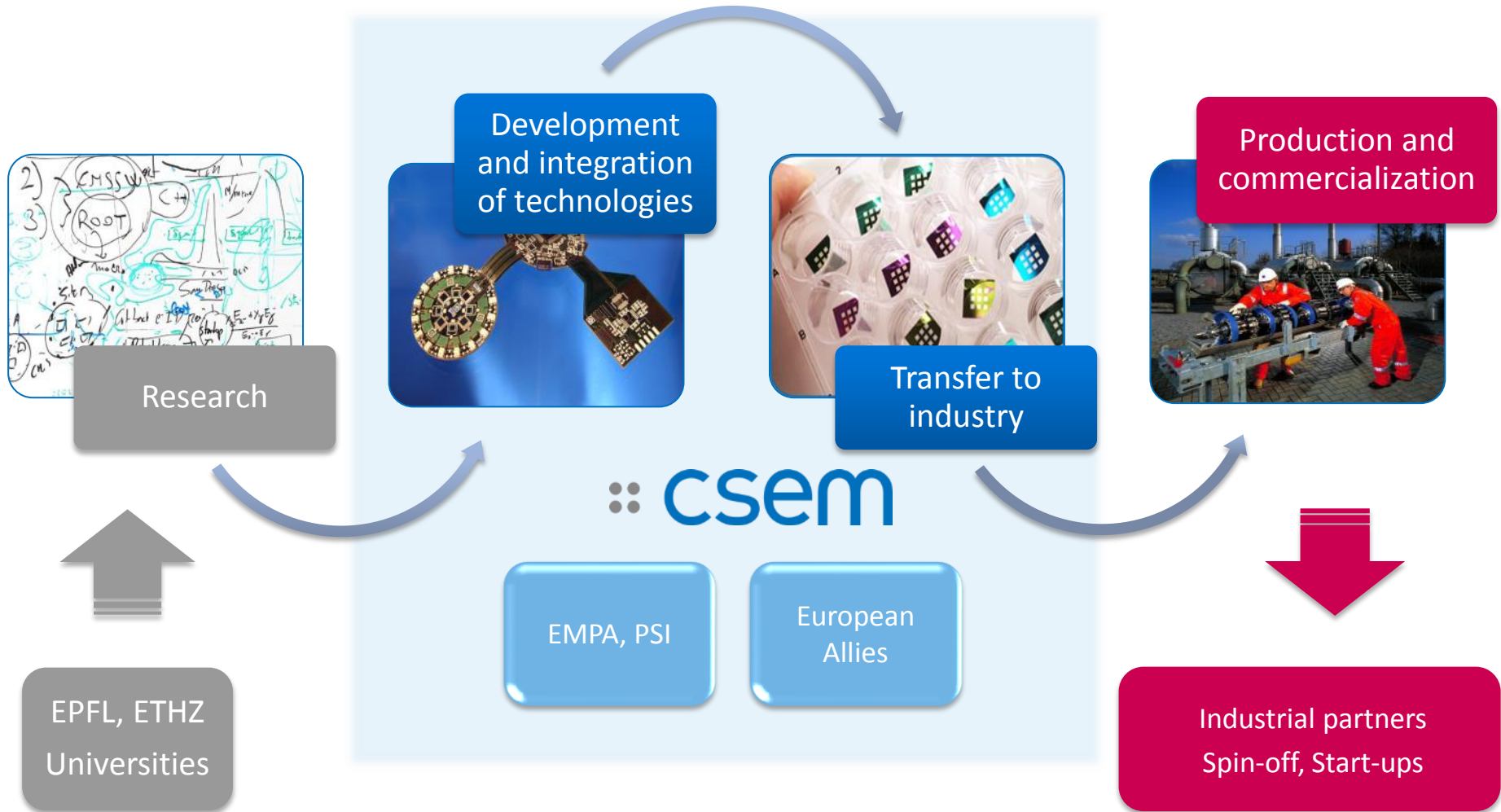


# CSEM at a glance

- Incorporated, not-for-profit **Research and Technology Organization (RTO)**, supported by the Swiss Government
- **A public-private partnership**
  - 31 % public
  - 69 % private
- **Key figures (2012)**
  - Revenues ~ CHF 70.0 mio
  - Employees ~ 400



# CSEM's positioning

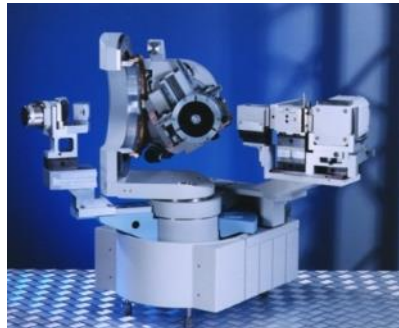


# Closer to industry ...



# Reliability-Analytical Laboratory @ CSEM

Two Units with complementary competencies



SMN: Service Micro & Nanoscopy

XRD: X-ray Diffraction

Our objectives:

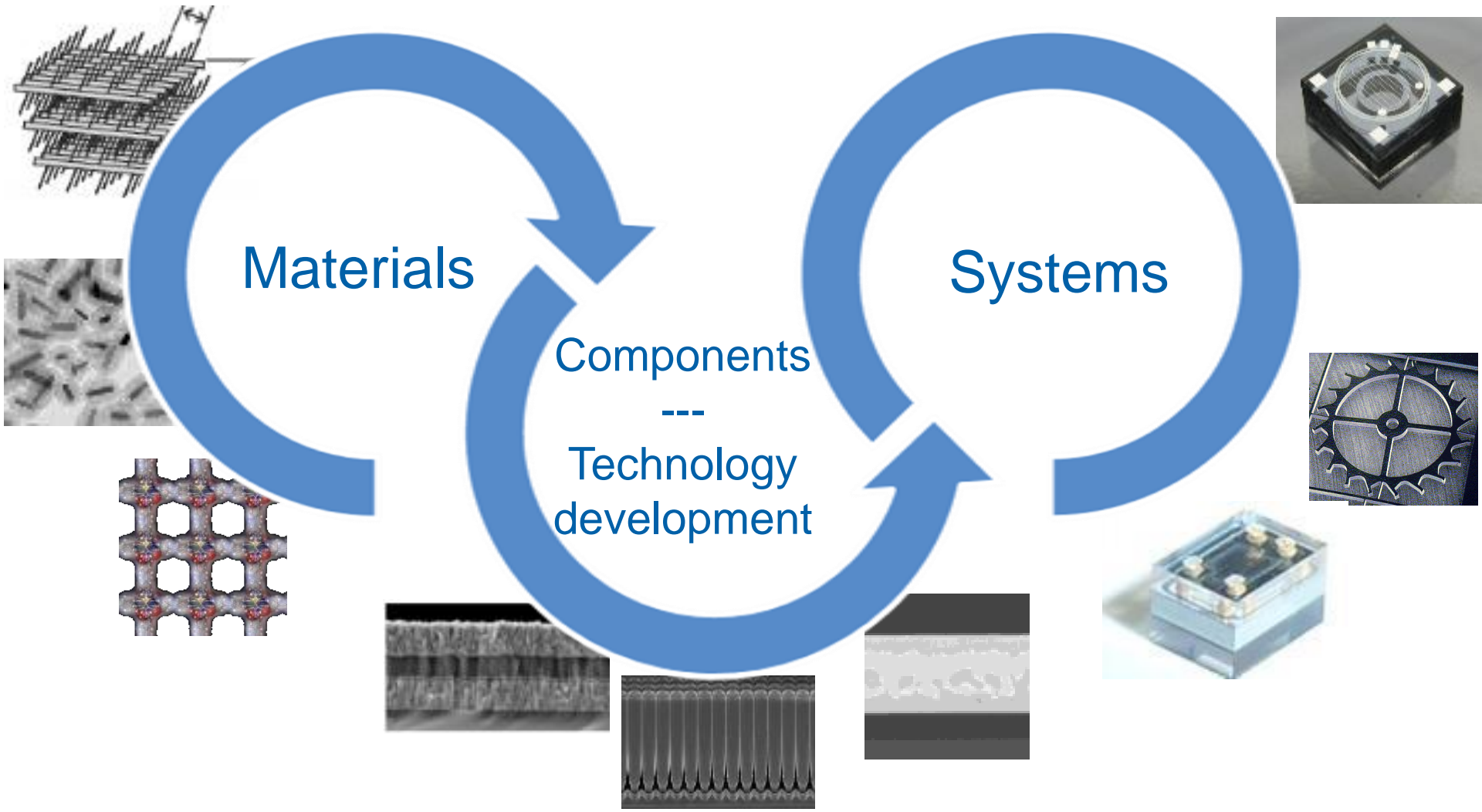
Technology support & services for our clients

Establishment of new qualification methods

Development of new analytical tools for process support

Reliability and Testing of Microsystems

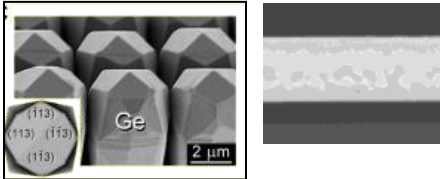
# Our Domain of Activities



# Technology Development Support

## Materials & Components

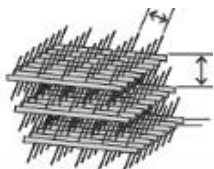
- Semiconductors & intermetallics



- Oxide & nitride coatings



- Organic thin films



➤ ....

## Properties

- Structural

XRD methods & Microscopy

In-situ techniques:  
 - Temperature,  
 - Humidity,  
 - Reactions,  
 - Mechanical forces

- Mechanical
- Electrical

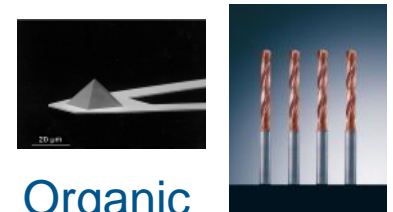
➤ ....

## Systems / Application

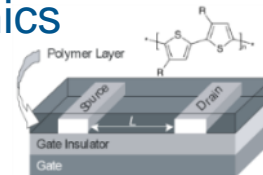
- Microsystems



- Tools



- Organic electronics

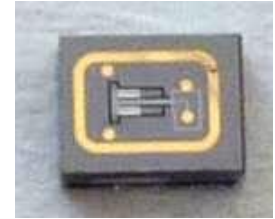
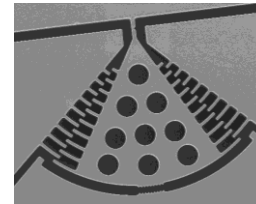
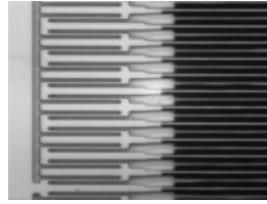
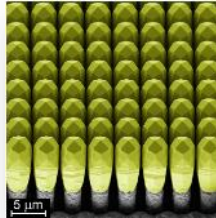
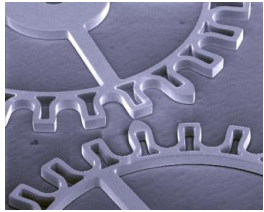


➤ ....

# Technology Development Support



## Qualification of subcomponents, components and devices



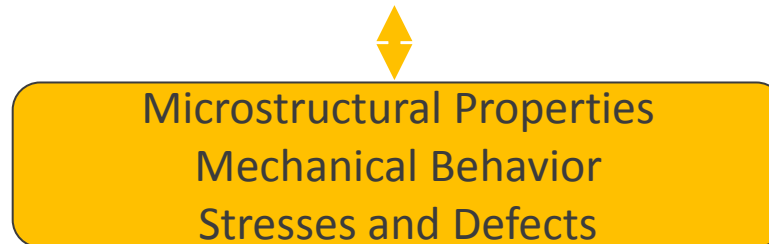
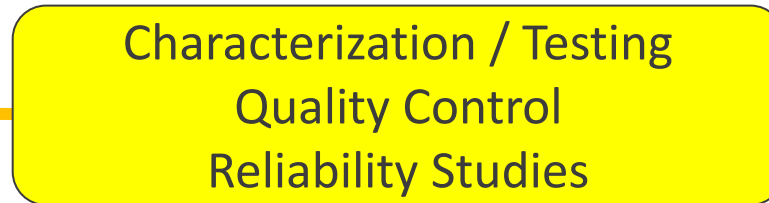
Concept  
Phase

Design  
Phase

Components  
Fabrication

Components Assembly  
& Packaging

Micro-  
system



# Micro and Nanoscopy



**Philips CM200**  
(Resolution 0.14 nm)

- EDS
- EBSD
- insitu deformation testing
- several cooling and heating stages



**Philips XL30 ESEM-FEG**, Resolution 2nm



**Nanoscope ICON**

# XRD Application Laboratory



Nano-crystalline materials

Micro-crystalline materials

Single crystalline materials.

*PANalytical X'Pert PRO MPD; MRD; STOE STADI P; IPDS I; IPDS II*

**Coatings:** Metal oxides, nitrides

**Thin films:** Molecular self-assembling organics

**Interfaces:** Joining materials

**Microsystems:** Quality Control and Reliability

## Analysis:

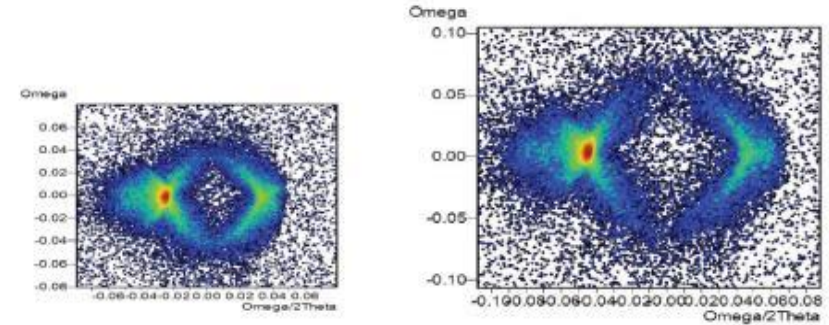
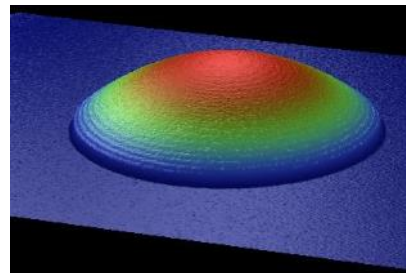
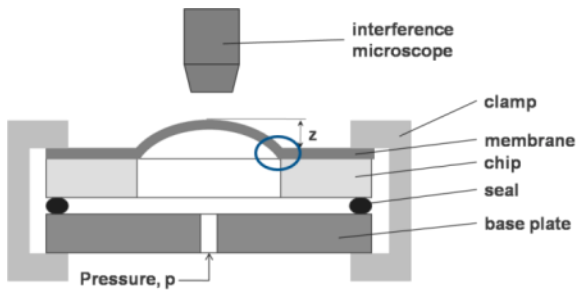
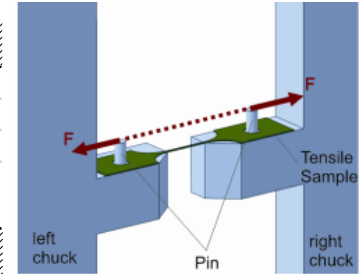
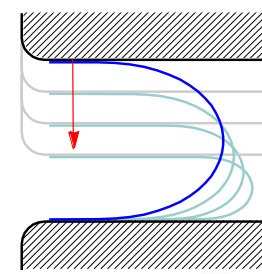
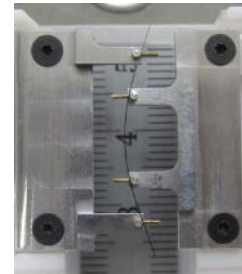
- Phases
- Stresses (HRXRD)
- Defects (HRXRD)
- Texture
- Grain sizes and distributions

# Reliability and Testing of Microsystems @ CSEM

## Materials Analysis: Stresses & Defects, Mechanical behavior, Microstructural properties

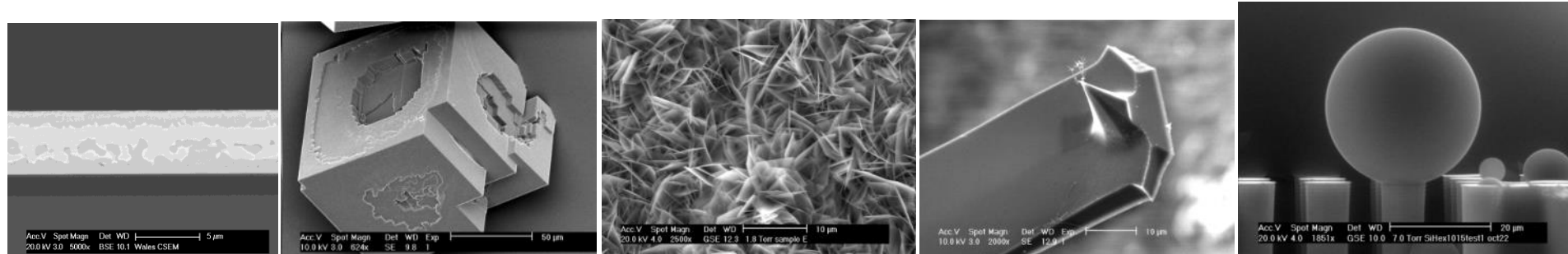
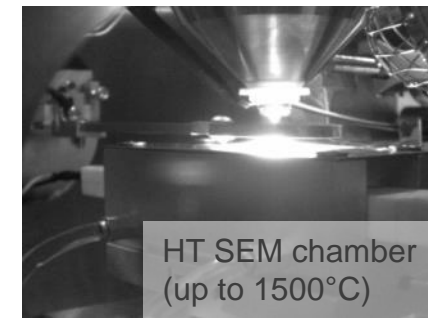
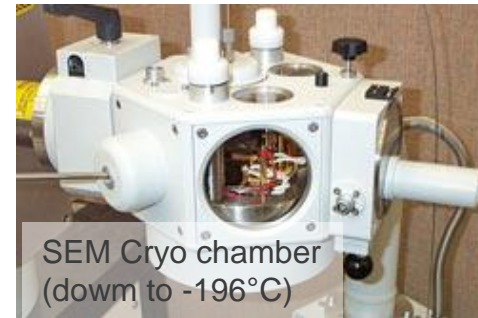
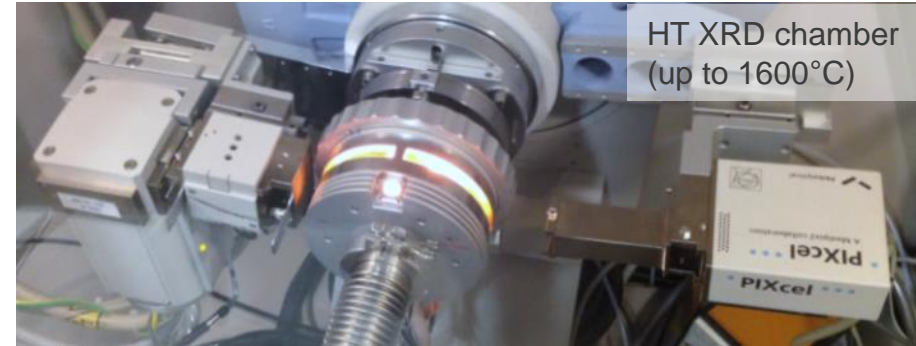


- ✓ Elastic modulus
- ✓ Poisson's ratio
- ✓ Fracture/failure mechanisms
- ✓ Fracture toughness
- ✓ Electrical properties (migration, etc.)
- ✓ Interfacial strength
- ✓ Coefficient of thermal expansion (CTE)
- ✓ *Crystal structure*
- ✓ *Grain size*
- ✓ *Surface roughness*
- ✓ *Doping*



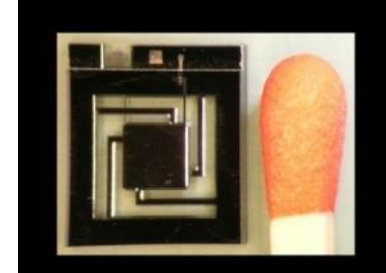
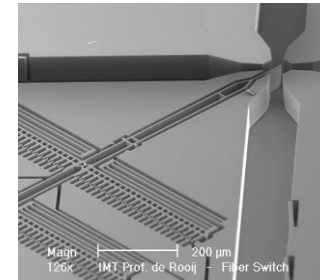
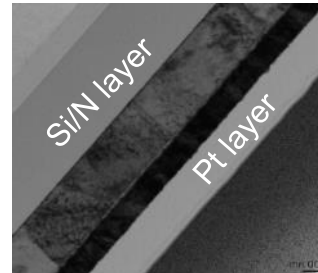
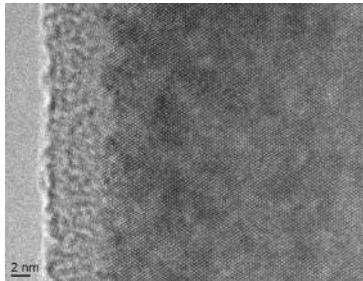
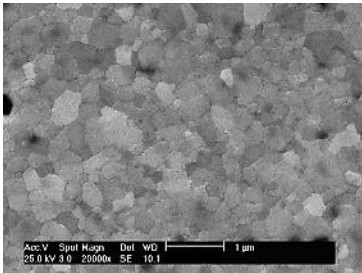
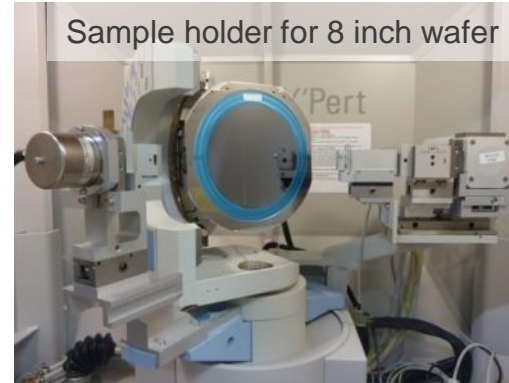
## Environmental Effects

- ✓ Storage, humidity effects
- ✓ Radiation tolerance
- ✓ Chemical exposure effects
- ✓ Biocompatibility
- ✓ Effects of extreme heat or cold
- ✓ Effect of shock



## Device-Level Metrology

- ✓ *High resolution cross-sectioning*
- ✓ *Microscale crack propagation visualization*
- ✓ *Real time performance (movement) visualization*
- ✓ *Device design effects (corners, etch holes, etc.)*



## Device-Level Metrology

### Fabrication:

1) Si structuring:  
DRIE

Defects

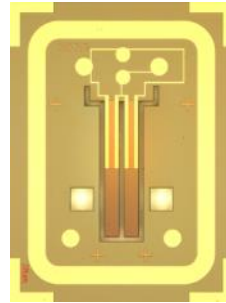
2) Layer deposition:  
AlN, ...

Texture

Phase  
Analysis

Crystallite  
Sizes

Layer stress

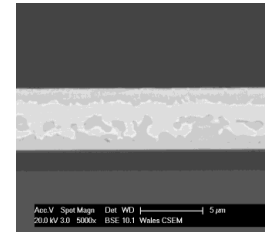


**MEMS  
resonator**

### Packaging:

3) Sealing at 320°C

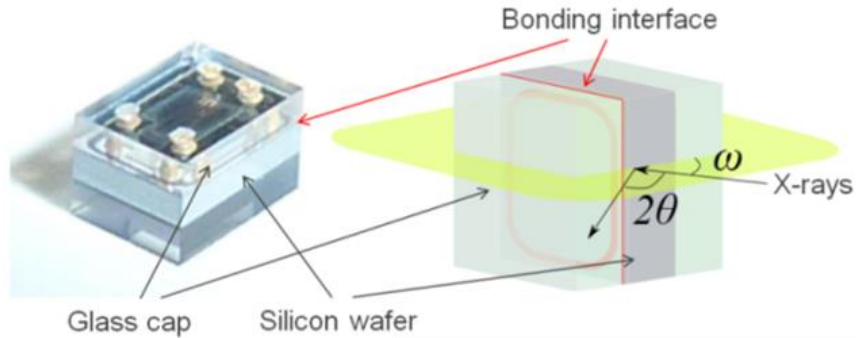
In-situ T-dependent  
XRD studies



Packaging Stress

Defect Mobility

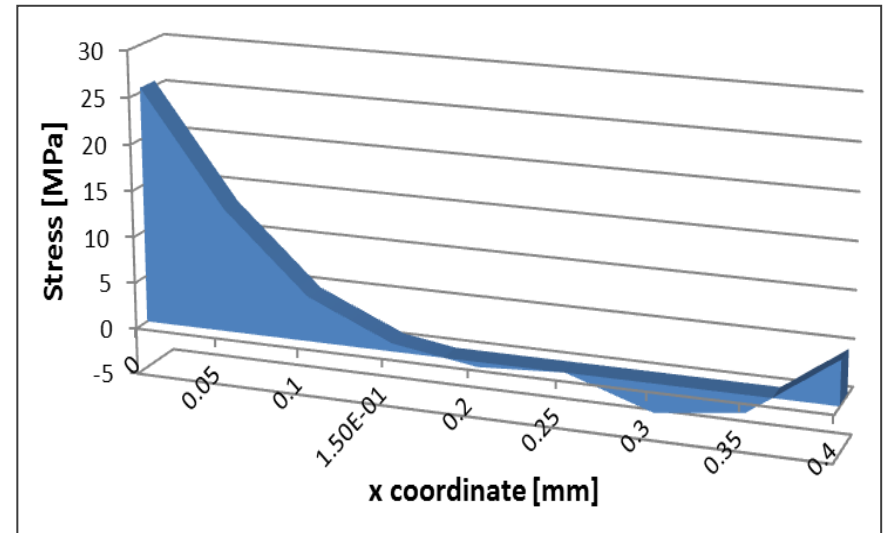
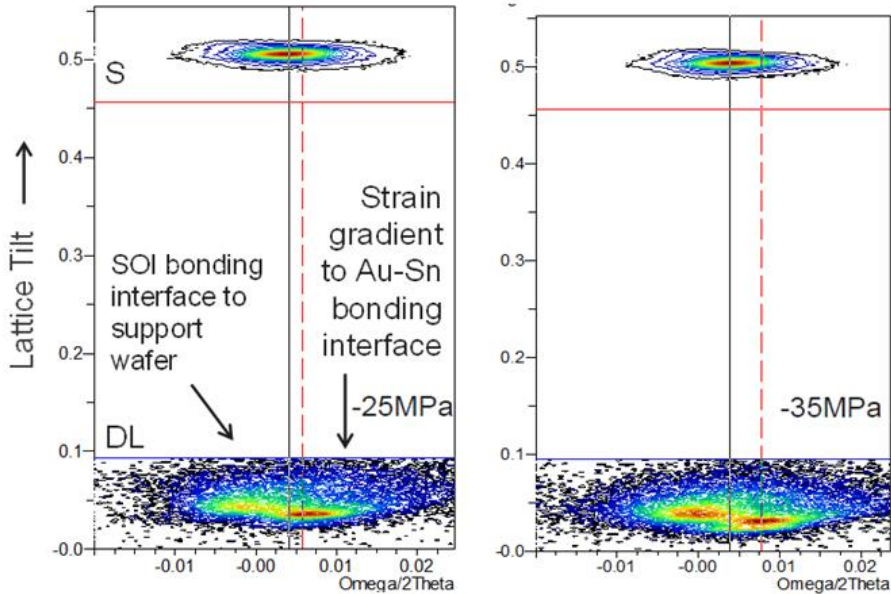
## Device-Level Metrology



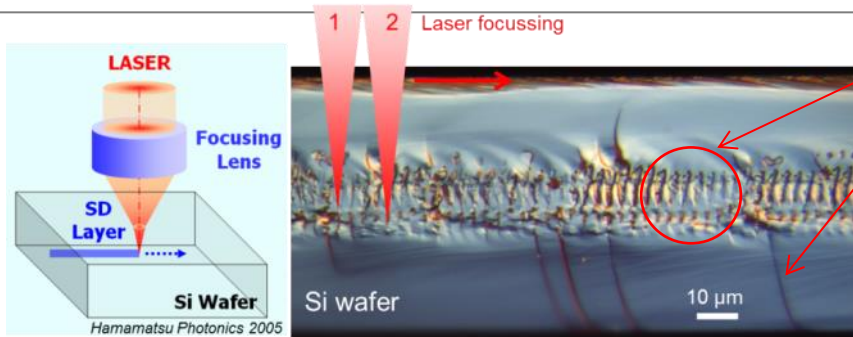
**Packaged device**

**Device without cap**

**Bonding interface**



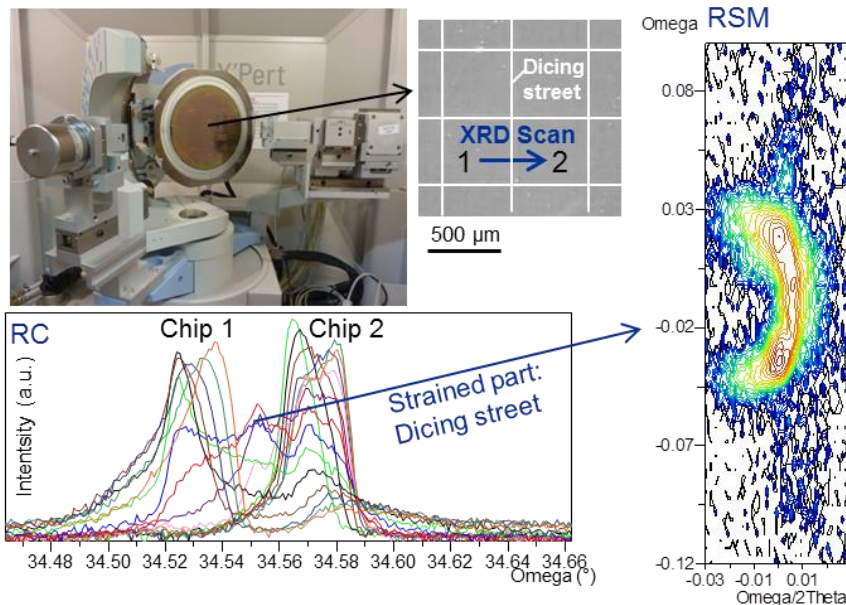
# Qualification of Laser Processes for Chip Separation using HRXRD and Micromechanical Testing



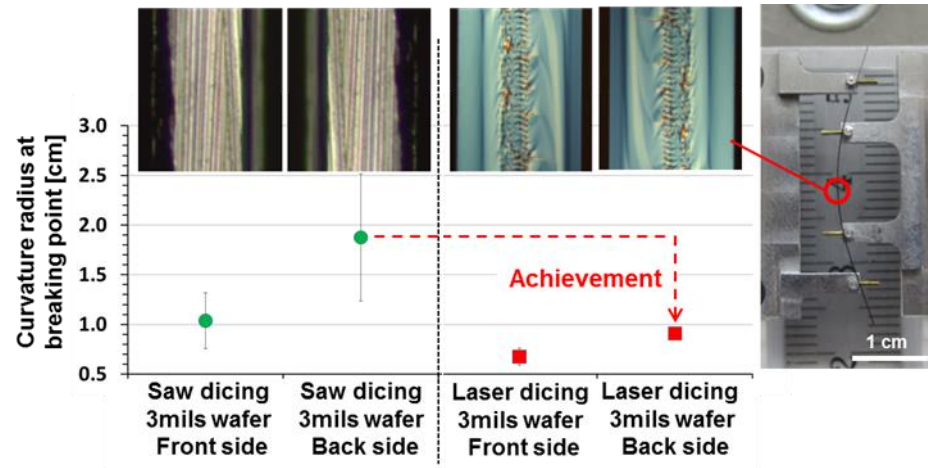
- High defect zone and amorphization of Si
- Radial fractures

How much do these defects affect the quality of the Si and therefore the reliability of the chip?  
 What are the best laser parameters to minimize these defects?

## Strain analyses with high resolution XRD

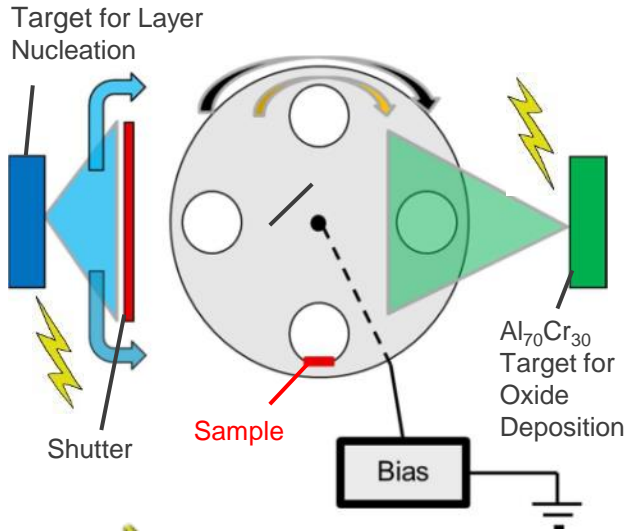


## Micromechanical testing



# Thin film deposition and characterization: Ex: Wear Resistant Hard Coatings

Reactive Cathodic Arc Deposition: Phases, Phase, transformations at HT, Texture, Stress, Grain size?



**EMPA**  
Materials Science & Technology

**oerlikon**  
balzers

**ETH**  
Eidgenössische Technische Hochschule Zürich  
Swiss Federal Institute of Technology Zurich

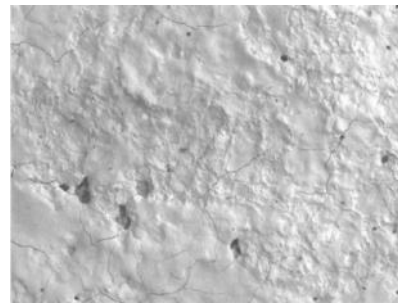


Pure Al and pure Hf

Cathodic arc process

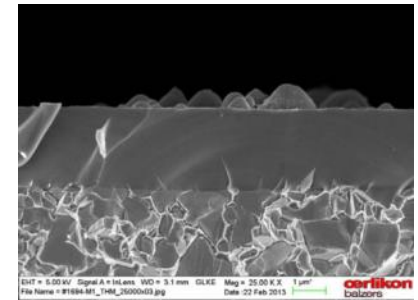


O<sub>2</sub>



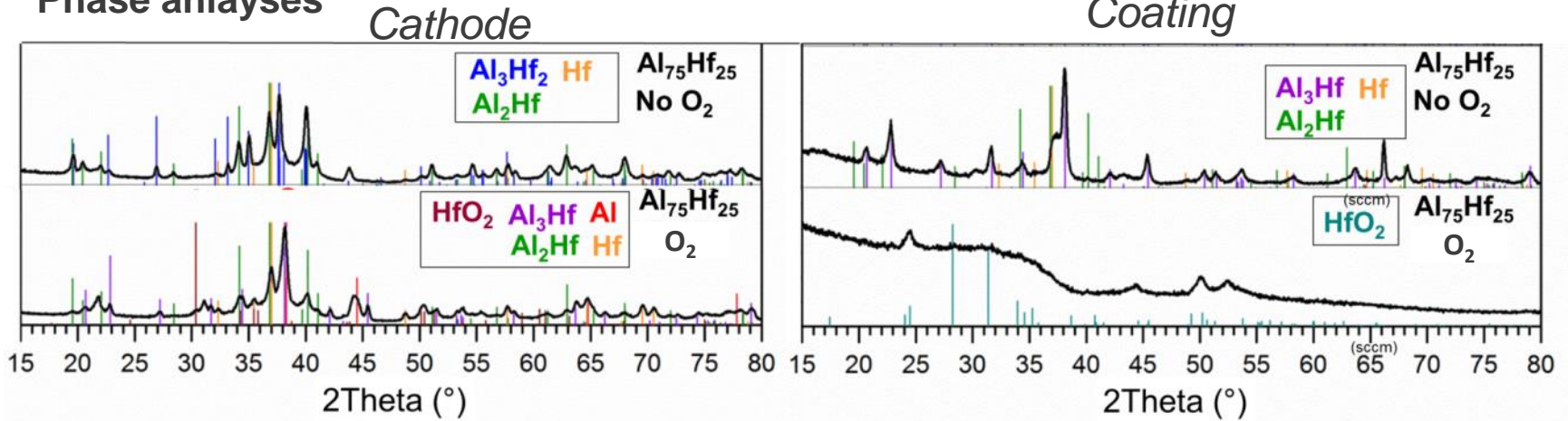
Intermetallics + Oxides

Deposition

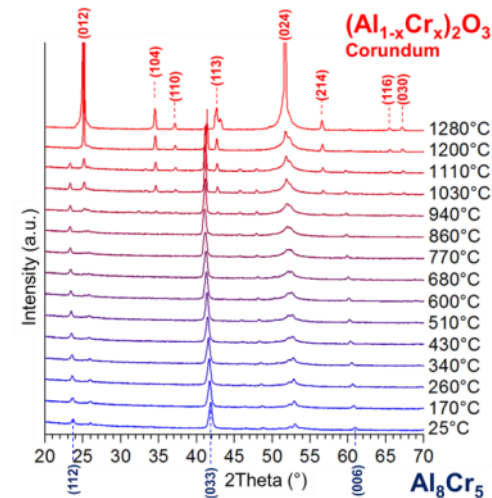
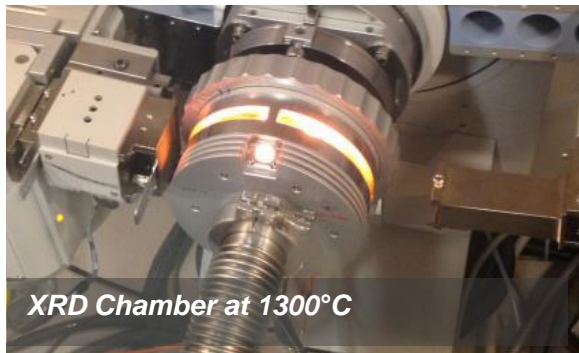


# Thin film deposition and characterization: Ex: Wear Resistant Hard Coatings

## Phase analyses

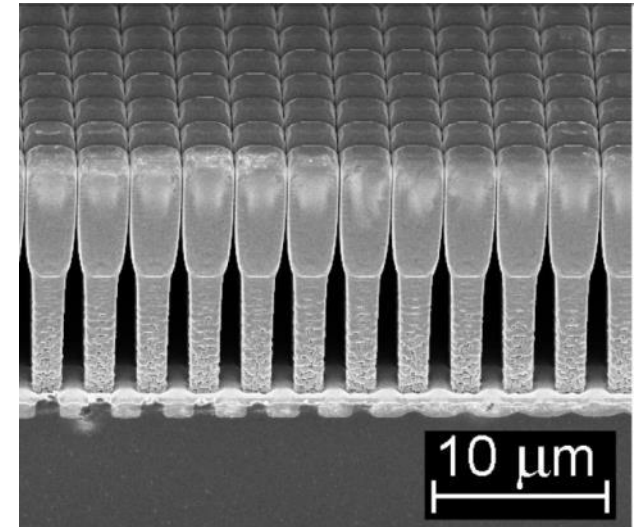
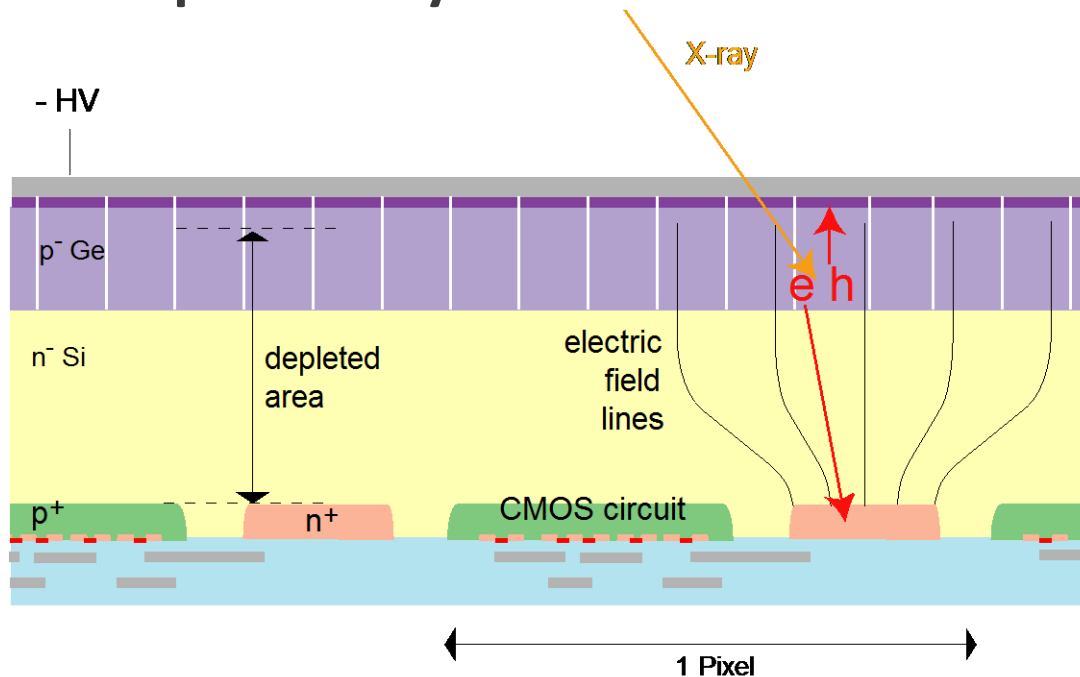


## Insitu high temperature studies



# New Types of X-ray detection systems

## Concept of X-ray Detector:

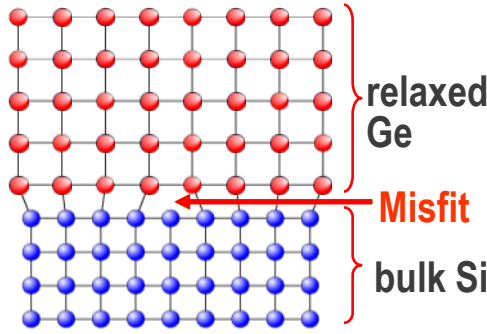


- Thick Ge layer (50 – 150  $\mu\text{m}$ )
- Epitaxially grown with LEPECVD on backside of CMOS wafer
- Ge absorption layer is hence monolithically integrated
- No bump-bonding needed

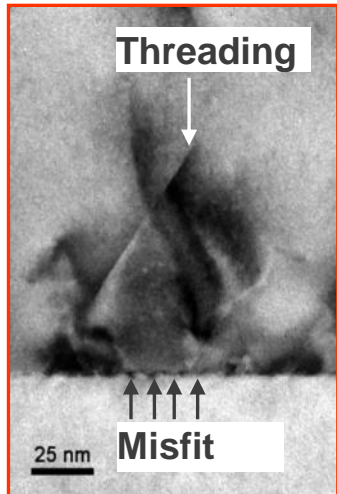
## Challenge



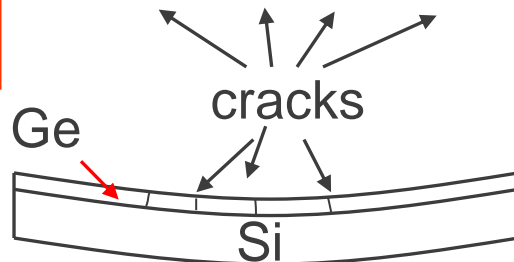
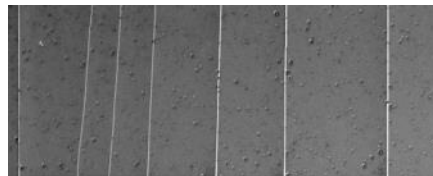
## Innovation



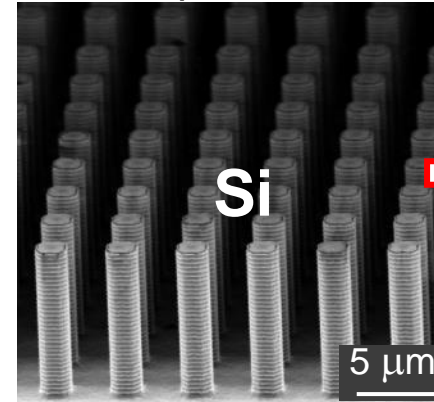
- Lattice mismatch (strain = 4.2 %)
- Mismatch of thermal expansion coefficients.



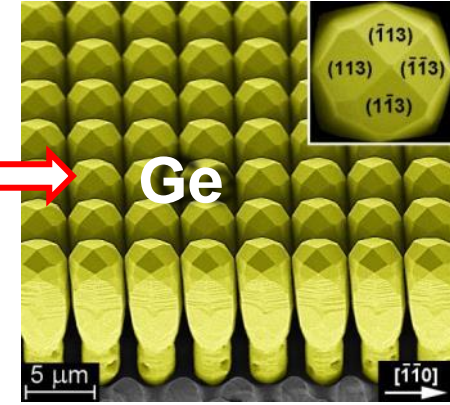
⇒ High density of misfit (MD) and threading (TD), wafer bowing and cracks



Micromachined Si pillars



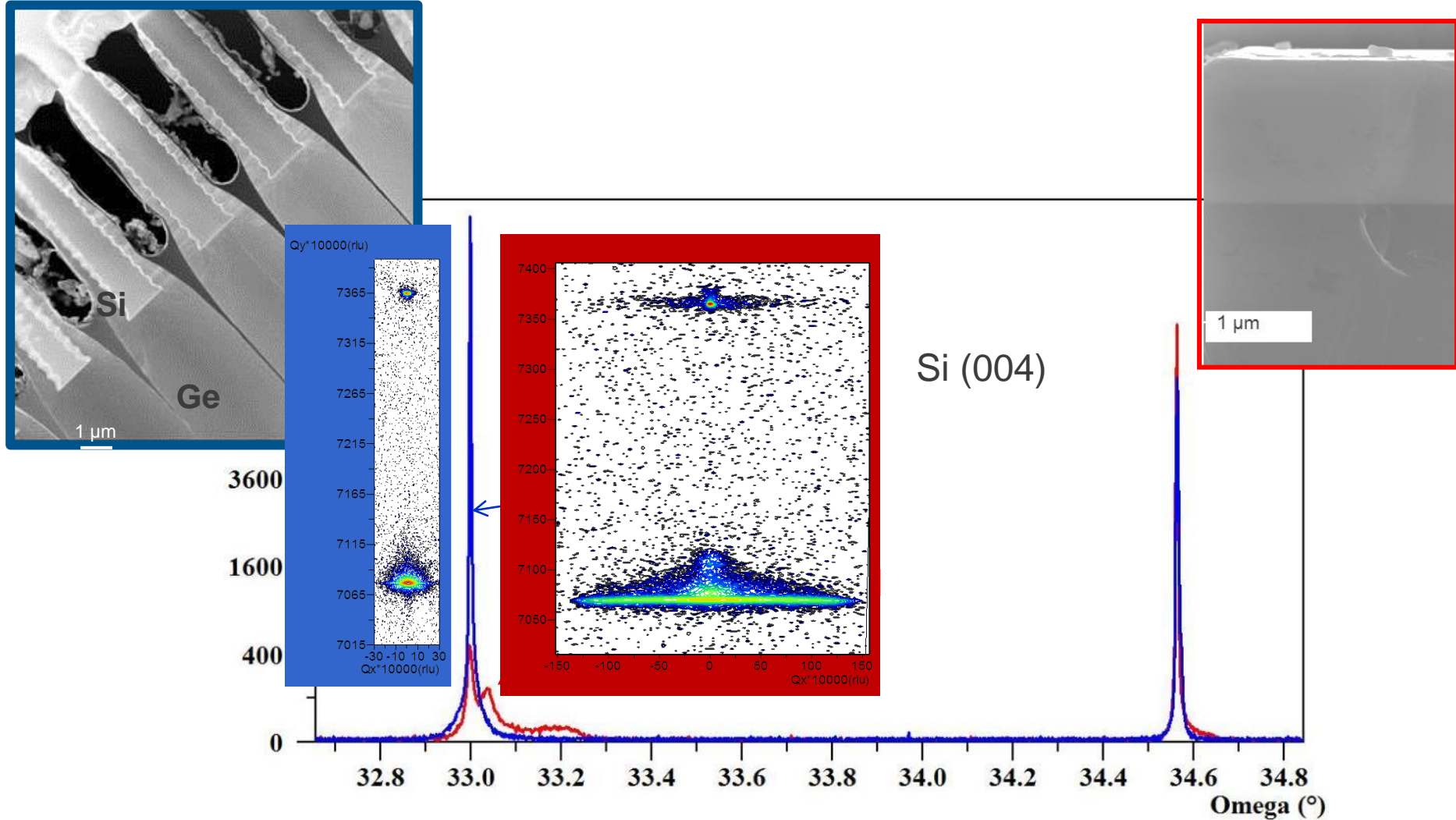
Epitaxial Ge pillars on Si



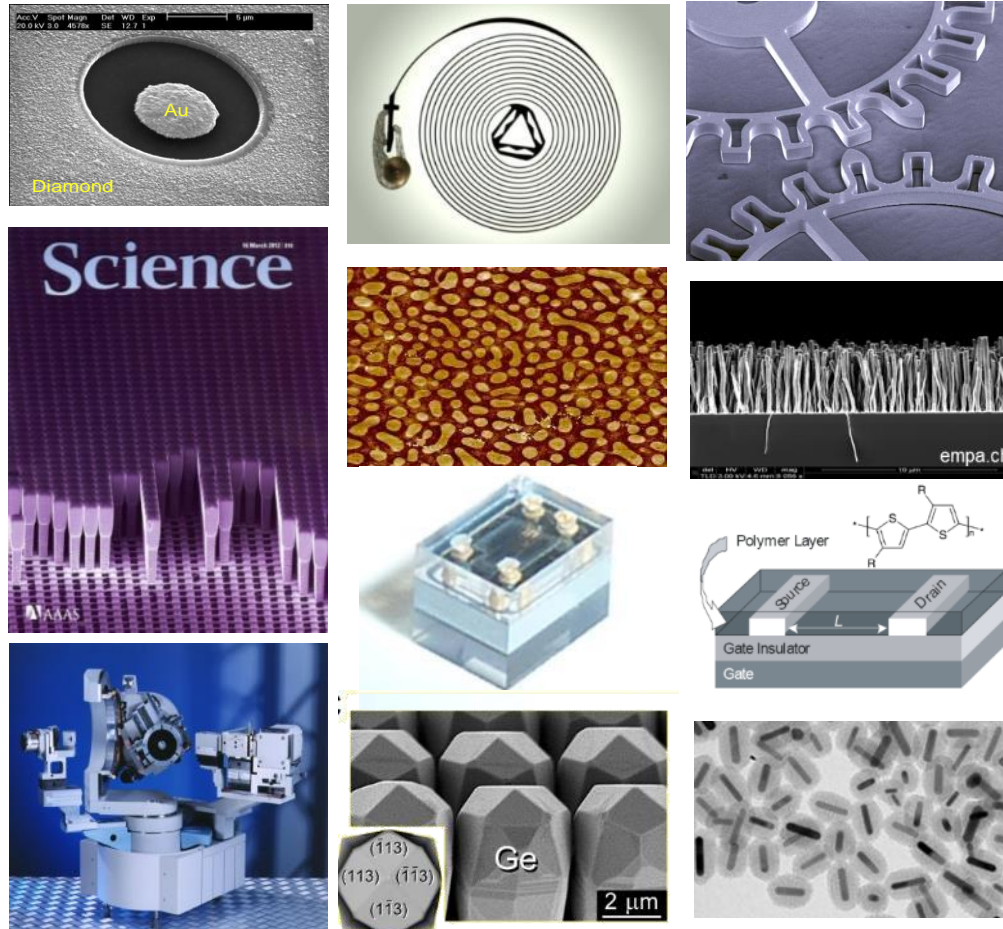
Low Energy Plasma Enhanced Chemical Vapor Deposition (LEPECVD) of Ge on Si pillars

*Falub et al. Science 2012*

# Strain analyses by HRXRD



# Technology development support :



Thank you for your attention